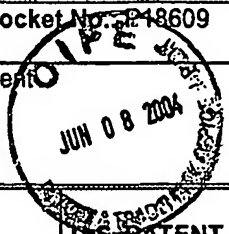


Form PTO-1449 (Modified)		Atty Docket No.: 218609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS			
Examiner Initials	Document No.	Class	Sub-Class	Filing date if appropriate		
CDW	AA	6,365,450 B1	Kim	438	216	
	AB					
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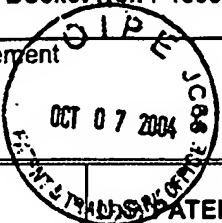
FOREIGN PATENT DOCUMENTS							
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AP							
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AS	
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Examiner <i>Christian Wilson</i>	Date Considered <i>11/9/05</i>
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



REFERENCE DESIGNATION						
Examiner Initials	Document No.	Class	Sub-Class	Filing date if appropriate		
DW	AA	6,255,698 B1	Gardner et al.	257	369	
	AB	6,410,376 B1	Ng et al.	438	199	
DW	AC	6,586,288 B2	Kim et al.	438	183	
	AD	US 2002/0058374 A1	Kim et al.	438	228	
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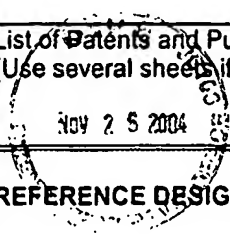
FOREIGN PATENT DOCUMENTS							
Document No.	Date	Country	Class	Sub-Class	Translation		
DW AP EP 0 899 784 AZ	3/3/1999	EP					
DW AQ GB 2 358 737 A	4/24/2001	UK					
AR							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
DW	AS	Metz et al., "A Method for Making a Semiconductor Device Having a High-K Gate Dielectric Layer and a Metal Gate Electrode", Serial No. 10/839,077, Filed May 4, 2004
	AT	
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Examiner <i>Christina Wilson</i>	Date Considered <i>11/9/05</i>
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS			
Examiner Initials	Document No.	Document No.	Class	Sub-Class	Filing date if appropriate	
cdw	AA	6,642,131 B2	Harada	438	591	
cdw	AB	6,667,246 B2	Mitsuhashi et al.	438	756	
cdw	AC	6,794,234 B2	Polishchuk et al.	438	199	
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FOREIGN PATENT DOCUMENTS							
No.	Document No.	Date	Country	Class	Sub-Class	Translation	
	AQ						
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
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Examiner <i>Christ Wilson</i>	Date Considered <i>11/9/05</i>
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Form PTO-1449 (Modified)

Atty Docket No.: P18609

Serial No.: 10/828,958

List of Patents and Publications Statement
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Applicant: Justin K. Brask et al.

Filing Date: April 20, 2004

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

Examiner Initials		Document No.		Class	Sub- Class	Filing date if appropriate
SW	AA	6,727,130 B2	Kim et al.	438	199	
	AB					
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FOREIGN PATENT DOCUMENTS

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	AQ						
	AR						

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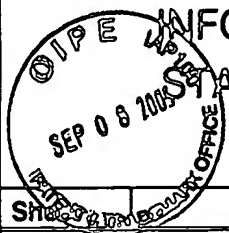
Examiner

Christina Wilson

Date Considered

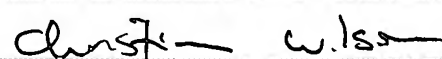
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Substitute for Form 1449/PTO <div style="float: left; width: 150px; text-align: center;">  </div> <div style="float: right; text-align: center;"> INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> </div> <div style="clear: both;"></div>				Complete if Known		
				Application Number	10/828,958	
				Filing Date	April 20, 2004	
				First Named Inventor:	Justin K. Brask et al.	
				Art Unit	Unknown 2891	
				Examiner Name	Unknown Wilson	
Sheet 1 of 2				Attorney Docket Number		P18609

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-	Number-Kind Code ² (if known)			
DW		US-	2001/0027005 A1	10/4/2001	Moriwaki et al.	
DW		US-	6,303,418 B1	10/16/2001	Cha et al.	
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ⁵ (if known)				
DW		WO	01/97257 A	12/20/2001	Madhukar, Kucharita		
DW		EP	1 032 033 A	8/30/2000	Wilks, Glen D.		
DW		JP	2002-118175 A	4/19/2002	Toshiba Corp.		

Examiner Signature		Date Considered	11/1/05
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: Unknown 10823958		
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask		
				Filing Date: April 20, 2004		
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS			
Examiner Initials	Document No.	Document No.	Class	Sub-Class	Filing date if appropriate	
<div style="text-align: center;"> </div>	AA	6,063,698	Tseng et al.	438	585	
	AB	6,184,072 B1	Kaushik et al.	438	197	
	AC	6,420,279 B1	Ono et al.	438	785	
	AD	6,475,874 B2	Xiang et al.	438	396	
	AE	6,514,828 B2	Ahn et al.	438	240	
	AF	6,544,906 B2	Rotondaro et al.	438	785	
	AG	6,617,209 B1	Chau et al.	438	240	
	AH	6,617,210 B1	Chau et al.	438	240	
	AI	6,620,713 B2	Arghavani et al.	438	585	
	AJ	6,689,675 B1	Parker et al.	438	585	
	AK	6,696,327 B1	Brask et al.	438	197	
	AL	6,696,345 B2	Chau et al.	438	387	
	AM	US2002/0197790 A1	Kizilyalli et al.	438	240	
	AN	US2003/0032303 A1	Yu et al.	438	770	
	AO	US2003/0045080 A1	Visokay et al.	438	591	
	FOREIGN PATENT DOCUMENTS					
	Document No.	Date	Country	Class	Sub-Class	Translation
AP						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)						
<div style="text-align: center;"> </div>	AQ	Polishchuk et al., "Dual Workfunction CMOS Gate Technology Based on Metal Interdiffusion", www.eesc.berkeley.edu , 1 page				
	AR	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages				
	AS	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page				
	AT	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hamburg-Harburg, 5 pages				
	AU	Doczy et al., "Integrating N-type and P-type Metal Gate Transistors," Serial No. 10/327,293, Filed December 20, 2002				
	AV	Brask et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode," Serial No. 10/704,497, Filed November 6, 2003				
	AW	Brask et al., "A Method for Etching a Thin Metal Layer," Serial No. 10/704,498, Filed November 6, 2003				
	AX	Brask et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Layer," Serial No. 10/742,678, Filed 12/19/03				
	AY	Brask et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/739,173, filed December 18, 2003				
	AZ	Brask et al., "A CMOS Device With Metal and Silicide Gate Electrodes and a Method for Making It," Serial No. 10/748,559, filed December 29, 2003				
	BA	Doczy et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/748,545, filed December 29, 2003				
	BB	Shah et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode," Serial No. 10/805,880, filed March 22, 2004				
	BC	Shah et al., "A Replacement Gate Process for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/809,853, filed March 24, 2004				
	Examiner	Christian Wilson		Date Considered 11/9/05		
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